

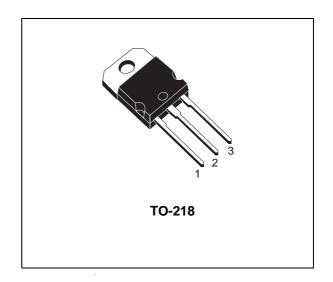
COMPLEMENTARY SILICON POWER TRANSISTORS

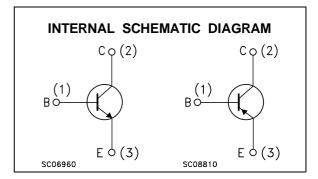
- STMicroelectronics PREFERRED SALESTYPES
- COMPLEMENTARY PNP NPN DEVICES

DESCRIPTION

The TIP3055 is a silicon Epitaxial-Base Planar NPN transistor mountend in TO-218 plastic package. It is intented for power switching circuits, series and shunt regulators, output stages and hi-fi amplifiers.

The complementary PNP type is the TIP2955.





ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
		PNP	TIP2955	
		NPN	TIP3055	
V _{CBO}	Collector-Base Voltage (I _E = 0)	•	100	V
V _{CEO}	Collector-Emitter Voltage (I _B = 0)		60	V
Ic	Collector Current		15	Α
Ι _Β	Base Current		7	Α
P _{tot}	Total Dissipation at T _c ≤ 25 °C		90	W
T _{stg}	Storage Temperature		-65 to 150	°C
Tj	Max. Operating Junction Temperature		150	°C

For PNP types voltage and current are negative.

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TIP2955/TIP3055

THERMAL DATA

ELECTRICAL CHARACTERISTICS ($T_{case} = 25$ $^{\circ}C$ unless otherwise specified)

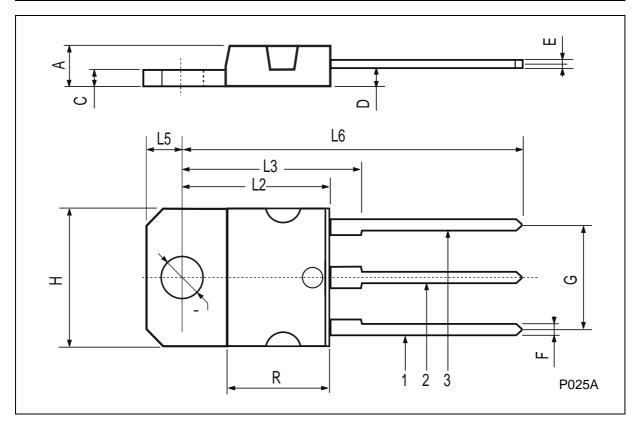
Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
I _{CEX}	Collector Cut-off Current (V _{BE} = -1.5V)	V _{CE} = 100 V V _{CE} = 100 V T _J = 150 °C			1 5	mA mA
I _{CEO}	Collector Cut-off Current (I _B = 0)	V _{CE} = 30 V			0.7	mA
I _{EBO}	Emitter Cut-off Current (I _C = 0)	V _{EB} = 7 V			5	mA
V _{CEO(sus)*}	Collector-Emitter Sustaining Voltage (I _B = 0)	I _C = 30 mA	60			V
V _{CE(sat)*}	Collector-emitter Saturation Voltage	I _C = 4 A			1 3	V
V _{BE} *	Base-emitter Voltage	$I_C = 4 A$ $V_{CE} = 4 V$			1.8	V
h _{FE} *	DC Current Gain	I _C = 4 A	20 5		70	
h _{fe}	Small Signal Current Gain	Ic = 1 A V _{CE} = 10 V f = 1 KHz	15			
f⊤	Transition-Frequency	$I_C = 0.5 \text{ A} V_{CE} = 10 \text{ V} f = 1 \text{ MHz}$	3			MHz
t _{on} t _{off}	RESISTIVE LOAD Turn-on Time Turn-off Time	$I_{C} = 6 \text{ A}$ $I_{B1} = -I_{B2} = 0.6 \text{ A}$ $V_{BE(off)} = -4 \text{ V}$		0.5 0.9		μs μs

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^{*} Pulsed: Pulse duration = 300 μs, duty cycle 1.5 % For PNP type, voltage and current value are negative.

TO-218 (SOT-93) MECHANICAL DATA

DIM.	mm		inch			
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А	4.7		4.9	0.185		0.193
С	1.17		1.37	0.046		0.054
D		2.5			0.098	
Е	0.5		0.78	0.019		0.030
F	1.1		1.3	0.043		0.051
G	10.8		11.1	0.425		0.437
Н	14.7		15.2	0.578		0.598
L2	_		16.2	_		0.637
L3		18			0.708	
L5	3.95		4.15	0.155		0.163
L6		31			1.220	
R	_		12.2	_		0.480
Ø	4		4.1	0.157		0.161



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